



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

## WBFBP-02C Plastic-Encapsulate Diodes

### DS751-40LED02 Schottky barrier Diodes

#### DESCRIPTION

Silicon epitaxial planar

#### FEATURES

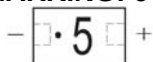
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

#### APPLICATION

High speed switching For Detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

#### MARKING: 5



#### WBFBP-02C

(1.0×0.6×0.5)

unit: mm



#### Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C

| Parameter                  | Symbol           | Limits  | Unit |
|----------------------------|------------------|---------|------|
| Peak reverse voltage       | V <sub>RM</sub>  | 40      | V    |
| DC reverse voltage         | V <sub>R</sub>   | 30      | V    |
| Mean rectifying current    | I <sub>O</sub>   | 30      | mA   |
| Peak forward surge current | I <sub>FSM</sub> | 150     | mA   |
| Junction temperature       | T <sub>j</sub>   | 125     | °C   |
| Storage temperature        | T <sub>stg</sub> | -40~125 | °C   |

#### Electrical Ratings @T<sub>A</sub>=25°C

| Parameter                     | Symbol         | Min. | Typ. | Max. | Unit | Conditions                |
|-------------------------------|----------------|------|------|------|------|---------------------------|
| Forward voltage               | V <sub>F</sub> |      |      | 0.37 | V    | I <sub>F</sub> =1mA       |
| Reverse current               | I <sub>R</sub> |      |      | 0.5  | μA   | V <sub>R</sub> =30V       |
| Capacitance between terminals | C <sub>T</sub> |      | 2    |      | pF   | V <sub>R</sub> =1V,f=1MHZ |

# Typical Characteristics

## ●Electrical characteristic curves ( $T_a = 25^\circ\text{C}$ )

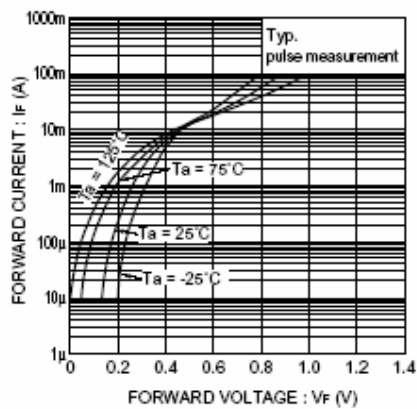


Fig. 1 Forward characteristics

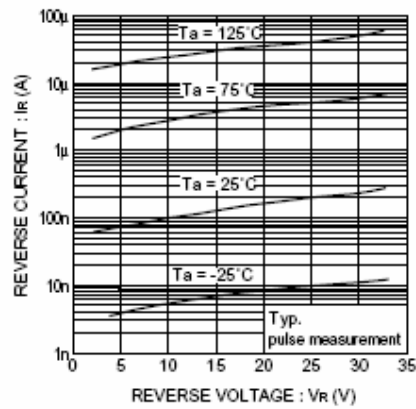


Fig. 2 Reverse characteristics

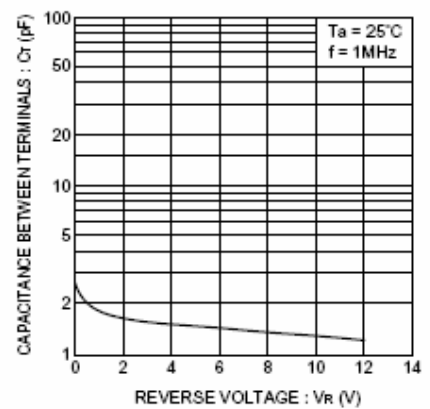


Fig. 3 Capacitance between terminals characteristics